

STSA1805

LOW VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

PRELIMINARY DATA

Ordering Code	Marking	Package / Shipment		
STSA1805	SA1805	TO-92 / Bulk		
STSA1805-AP	SA1805	TO-92 / Ammopack		

- VERY LOW COLLECTOR TO EMITTER SATURATION VOLTAGE
- HIGH CURRENT GAIN CHARACTERISTIC
- FAST-SWITCHING SPEED

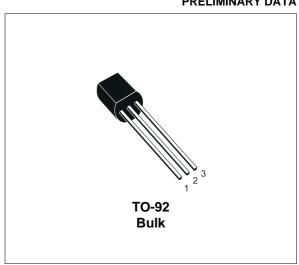
APPLICATIONS:

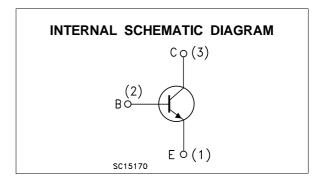
- EMERGENCY LIGHTING
- VOLTAGE REGULATORS
- RELAY DRIVERS
- HIGH EFFICIENCY LOW VOLTAGE SWITCHING APPLICATIONS



The device is manufactured in NPN Planar Technology by using a "Base Island" layout.

The resulting Transistor shows exceptional high gain performance coupled with very low saturation voltage.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	150	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	60	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	7	V
Ic	Collector Current	5	А
I _{CM}	Collector Peak Current (t _p < 5 ms)	15	А
I _B	Base Current	2	А
P _{tot}	Total Dissipation at T _{amb} = 25 °C	1.1	W
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

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THERMAL DATA

R _{thj-amb}	Thermal Resistance Junction-Ambient	Max	114	°C/W
R _{thj-case}	Thermal Resistance Junction-case	Max	83.3	°C/W

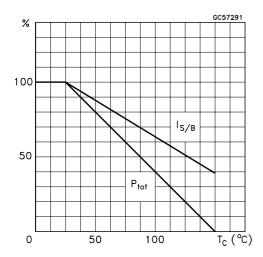
ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = 40 V				0.1	μΑ
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 4 V				0.1	μΑ
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	Ι _C = 100 μΑ		150			V
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = 1 mA		60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	Ι _Ε = 100 μΑ		7			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 100 mA I _C = 2 A I _C = 3 A I _C = 5 A	I_B = 5 mA I_B = 50 mA I_B = 150 mA I_B = 200 mA		150 200	50 300 400 600	mV mV mV
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 2 A	I _B = 100 mA		0.9	1.2	V
h _{FE} *	DC Current Gain	I _C = 100 mA I _C = 5 A I _C = 10 A	V _{CE} = 2 V V _{CE} = 2 V V _{CE} = 2 V	200 85 20		400	
f _T	Transition frequency	V _{CE} = 10 V	$I_C = 50 \text{ mA}$		150		MHz
Ссво	Collector-Base Capacitance	V _{CB} = 10 V	f = 1 MHz		50		pF
t _{on} t _s t _f	RESISTIVE LOAD Turn- on Time Storage Time Fall Time	I _C = 1 A I _{B1} = - I _{B2} = 0.1 A	V _{CC} = 30 V		50 1.35 120		ns µs ns

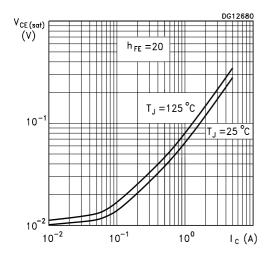
^{*} Pulsed: Pulse duration = 300μs, duty cycle = 1.5 %

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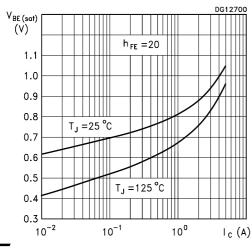
Derating Curve



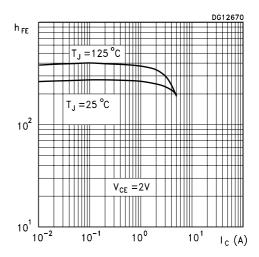
Collector-Emitter Saturation Voltage



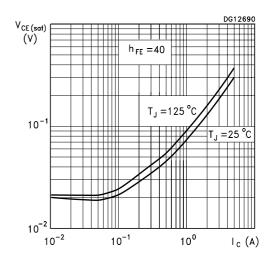
Base-Emitter Saturation Voltage



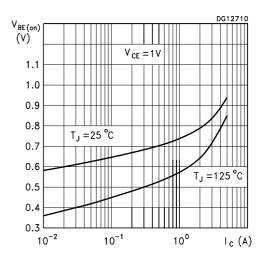
DC Current Gain



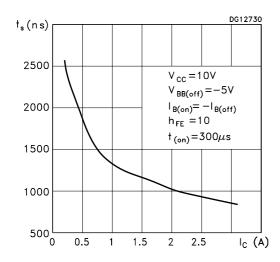
Collector-Emitter Saturation Voltage



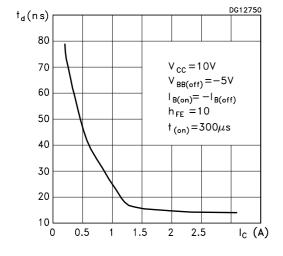
Base-Emitter On Voltage



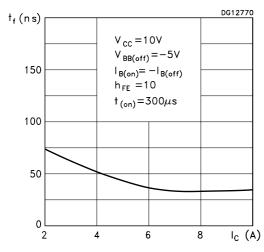
Switching Times Resistive Load



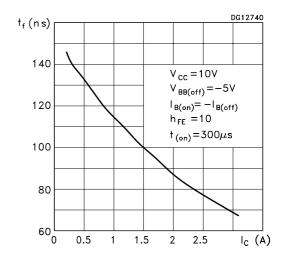
Switching Times Resistive Load



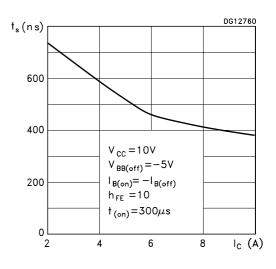
Switching Times Inductive Load



Switching Times Resistive Load

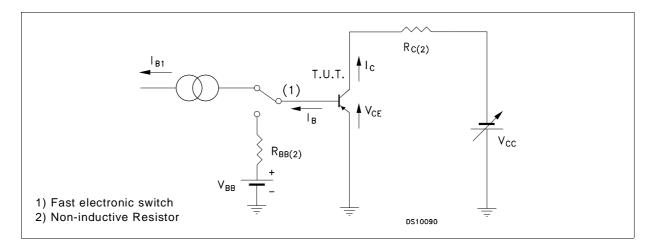


Switching Times Inductive Load



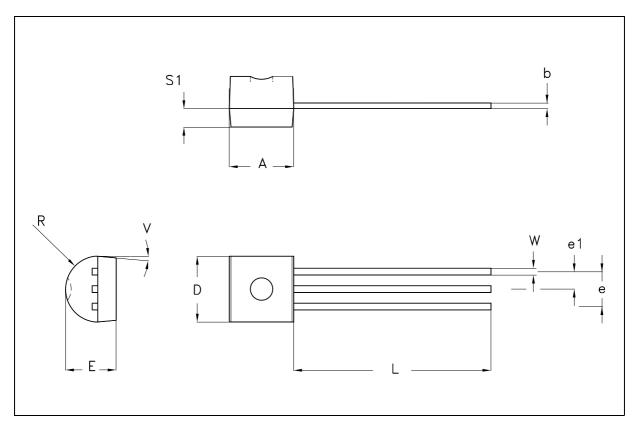
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Figure 1: Resistive Load Switching Test Circuit.



TO-92 MECHANICAL DATA

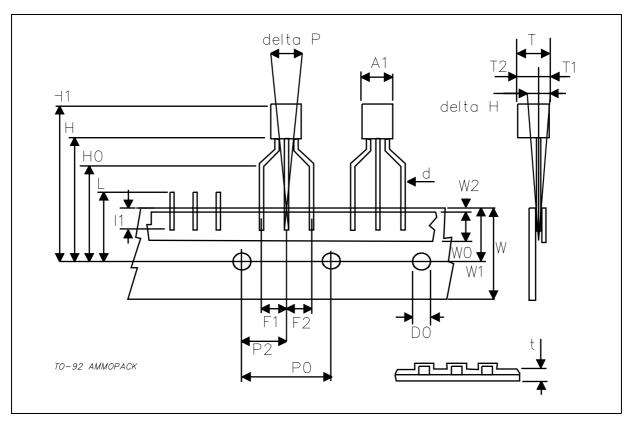
DIM.	mm			inch			
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	4.32		4.95	0.170		0.195	
b	0.36		0.51	0.014		0.020	
D	4.45		4.95	0.175		0.194	
Е	3.30		3.94	0.130		0.155	
е	2.41		2.67	0.095		0.105	
e1	1.14		1.40	0.045		0.055	
L	12.70		15.49	0.500		0.609	
R	2.16		2.41	0.085		0.094	
S1	1.14		1.52	0.045		0.059	
W	0.41		0.56	0.016		0.022	
V	4 degree		6 degree	4 degree		6 degree	



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TO-92 AMMOPACK SHIPMENT (Suffix"-AP") MECHANICAL DATA

DIM.	mm			inch			
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
A1			4.80			0.189	
T			3.80			0.150	
T1			1.60			0.063	
T2			2.30			0.091	
d			0.48			0.019	
P0	12.50	12.70	12.90	0.492	0.500	0.508	
P2	5.65	6.35	7.05	0.222	0.250	0.278	
F1,F2	2.44	2.54	2.94	0.096	0.100	0.116	
delta H	-2.00		2.00	-0.079		0.079	
W	17.50	18.00	19.00	0.689	0.709	0.748	
W0	5.70	6.00	6.30	0.224	0.236	0.248	
W1	8.50	9.00	9.25	0.335	0.354	0.364	
W2			0.50			0.020	
Н	18.50		20.50	0.728		0.807	
H0	15.50	16.00	16.50	0.610	0.630	0.650	
H1			25.00			0.984	
D0	3.80	4.00	4.20	0.150	0.157	0.165	
t			0.90			0.035	
L			11.00			0.433	
l1	3.00			0.118			
delta P	-1.00		1.00	-0.039		0.039	



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